UNISONIC TECHNOLOGIES CO., LTD

2SC4552

NPN SILICON TRANSISTOR

BIPOLAR SILICON NPN POWER TRANSISTOR

DESCRIPTION

The UTC 2SC4552 is a power transistor developed for high-speed switching and features low V_{CE(SAT)} and high hFE. This transistor is ideal for use in drivers such as DC/DC converters and actuators. In addition, a small resin-molded insulation type package contributes to high-density mounting and reduction of mounting cost.

TO-220F

FEATURES

* Collector-Emitter Sustaining Voltage:

V_{CEO(SUS)}= 60V (Min.)

* High DC Current Gain:

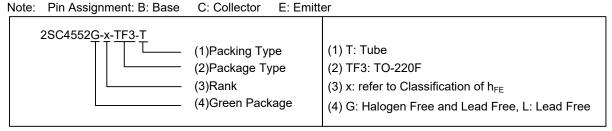
h_{FE}= 100(Min.) @ (V_{CE}= 2V, I_C= 3A)

* Low Saturation Voltage:

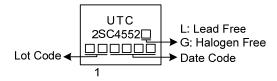
 $V_{CE(SAT)} = 0.3V \text{ (Max.)} @ (I_C = 8A, I_B = 0.4A)$

ORDERING INFORMATION

Ordering	Daalsana	Pin Assignment			Da alcina		
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SC4552L-x-TF3-T	2SC4552G-x-TF3-T	TO-220F	В	С	E	Tube	



MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	lc	15	Α
Pulse Collector Current	I _{CM}	30	Α
Continuous Base Current	I _B	7.5	Α
Collector Power Dissipation (T _C =25°C)	Pc	30	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	60			V
Collector-Emitter Sustaining Voltage	BV _{CEX}	I _C =1mA, V _{BE(OFF)} =-1.5V	60			V
Collector Cut-Off Current	Ісво	V _{CB} =60V, I _E =0			10	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5V, I _C =0			10	μΑ
Cut-Off Current	ICER	V _{CB} =60V, R _{BE} =50Ω, T _A =125°C			1.0	mA
Cut Off Current	I _{CEX}	V _{CB} =60V, V _{EB(OFF)} =-1.5V			10	μΑ
Cut-Off Current		V _{CB} =60V, V _{EB(OFF)} =-1.5V, T _A =125°C			1.0	mA
	h _{FE1}	V _{CE} =2V, I _C =1.5A	100			
DC Current Gain	h _{FE2}	V _{CE} =2V, I _C =3A	100		400	
	h _{FE3}	V _{CE} =2V, I _C =8A	60			
Calle star Fraitter Caturation Valtage	VCE(SAT)	I _C =8A, I _B =0.4A			0.5	V
Collector-Emitter Saturation Voltage		I _C =12A, I _B =0.6A			0.8	V
Bass Fraitter Caturation Valtage	VRE(SAT)	I _C =8A, I _B =0.4A			1.3	V
Base-Emitter Saturation Voltage		I _C =12A, I _B =0.6A			1.7	V

■ CLASSIFICATION OF h_{FE2}

RANK	M	L	K	
RANGE	100 ~ 200	150 ~ 300	200 ~ 400	

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